



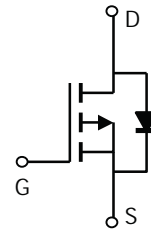
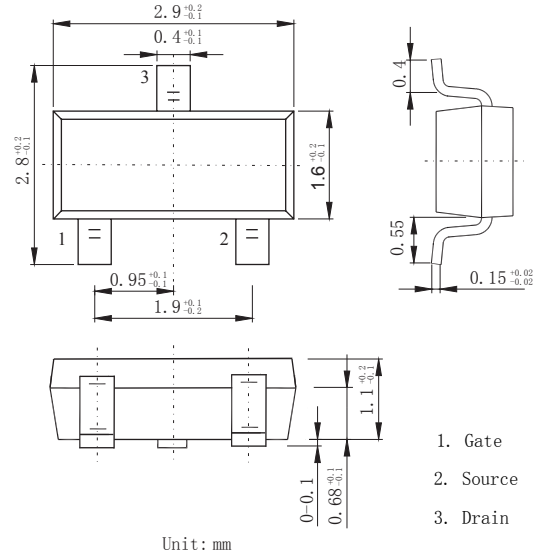
BC02P28TA

P-Channel MOSFET

SOT-23-3

Features

- $V_{DS} (V) = -20V$
- $R_{DS(ON)} < 28m\Omega$ ($V_{GS} = -4.5V$)
- $R_{DS(ON)} < 39m\Omega$ ($V_{GS} = -2.5V$)



Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	-7	A
Pulsed Drain Current (Note 1)	I_{DM}	-24	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	83	°C/W
---	-----------------	----	------

Electrical Characteristics (TA=25°C unless otherwise noted)

BC02P28TA

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.7	-1	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-6A$	-	21	28	m Ω
		$V_{GS}=-2.5V, I_D=-5A$	-	27	39	m Ω
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V,$ $F=1.0MHz$	-	990	-	pF
Output Capacitance	C_{oss}		-	115	-	pF
Reverse Transfer Capacitance (Note 4)	C_{rss}		-	88	-	pF
Gate Resistance	R_g		-	10	-	Ω
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=1\Omega,$ $V_{GS}=-4.5V, R_G=3\Omega$	-	14.2	-	nS
Turn-on Rise Time	t_r		-	7.6	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	38	-	nS
Turn-Off Fall Time	t_f		-	13.8	-	nS
Total Gate Charge	Q_g	$V_{DS}=-10V, I_D=-6A,$ $V_{GS}=-4.5V$	-	8.4	-	nC
Gate-Source Charge	Q_{gs}		-	2.6	-	nC
Gate-Drain Charge	Q_{gd}		-	1.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-1A$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-3	A
Body Diode Reverse Recovery Time	t_{rr}	$I_F=-6A, di/dt=100A/us$	-	28.1	-	nS
Body Diode Reverse Recovery Charge	Q_{rr}		-	7.9	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to product.

■ **Marking**

Marking	2317
---------	------

Typical Electrical and Thermal Characteristics

BC02P28TA

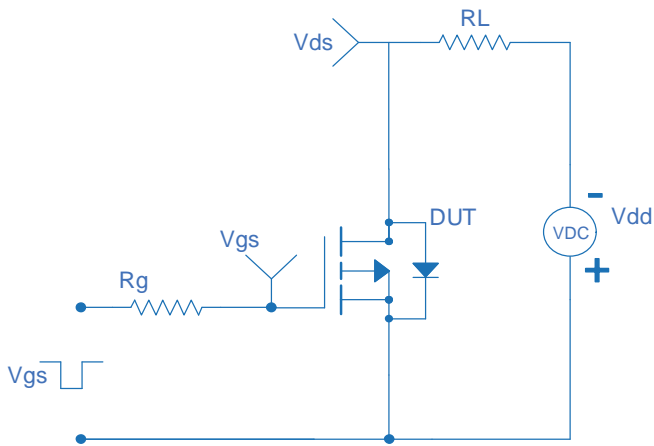


Figure 1 Switching Test Circuit

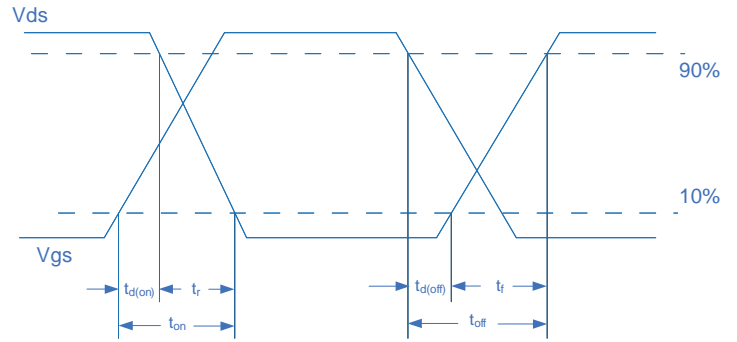


Figure 2 Switching Waveform

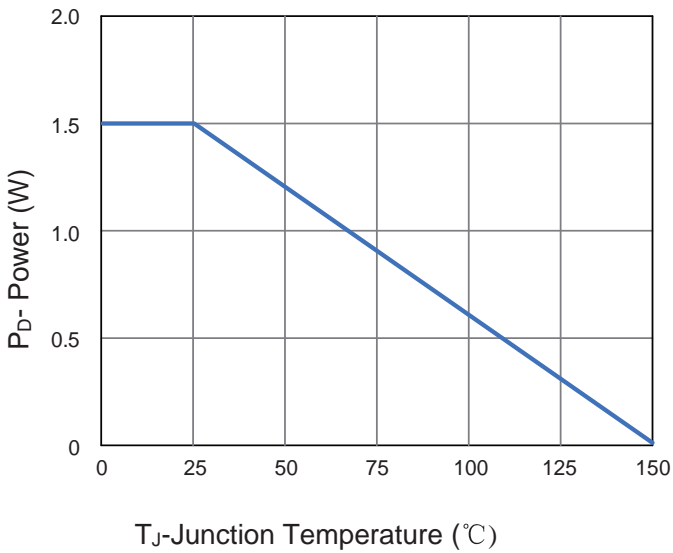


Figure 3 Power De-rating

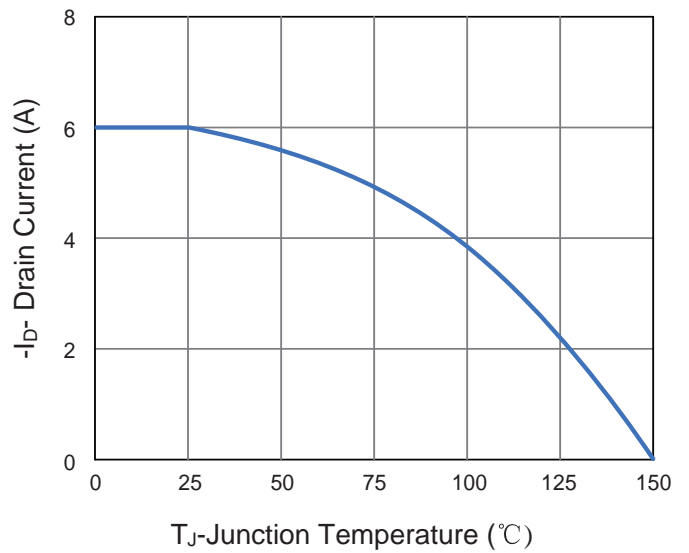


Figure 4 Drain Current

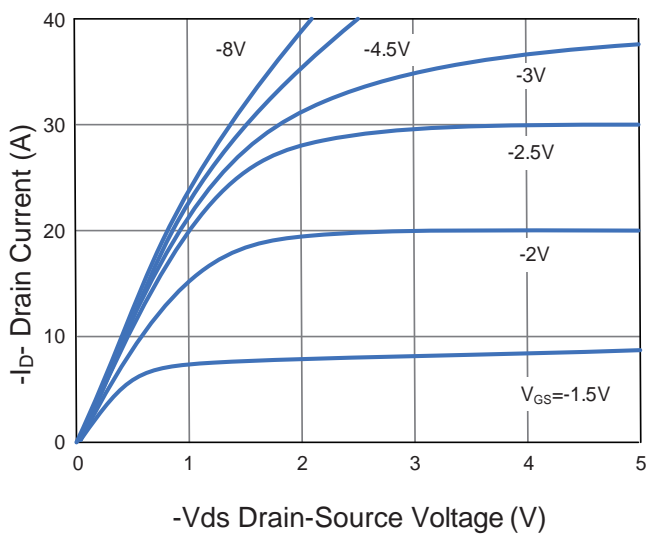


Figure 5 Output Characteristics

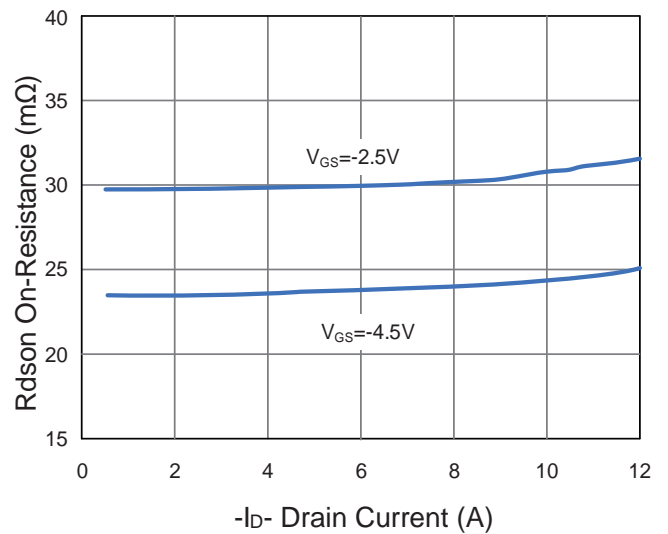


Figure 6 Rdson vs Drain Current

Typical Electrical and Thermal Characteristics

BC02P28TA

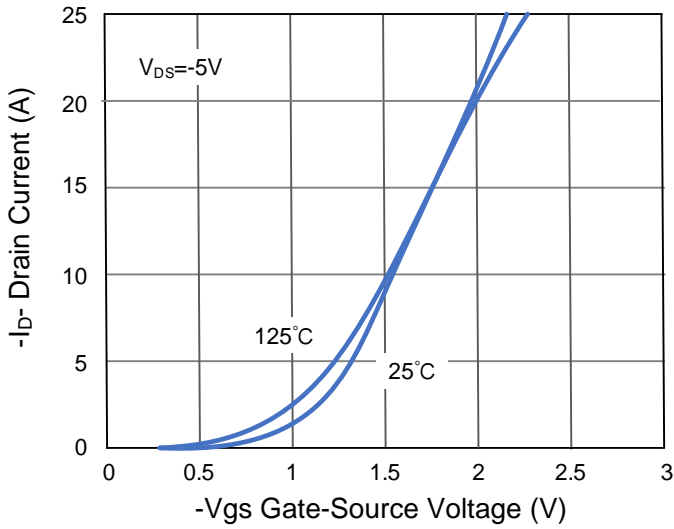


Figure 7 Transfer Characteristics

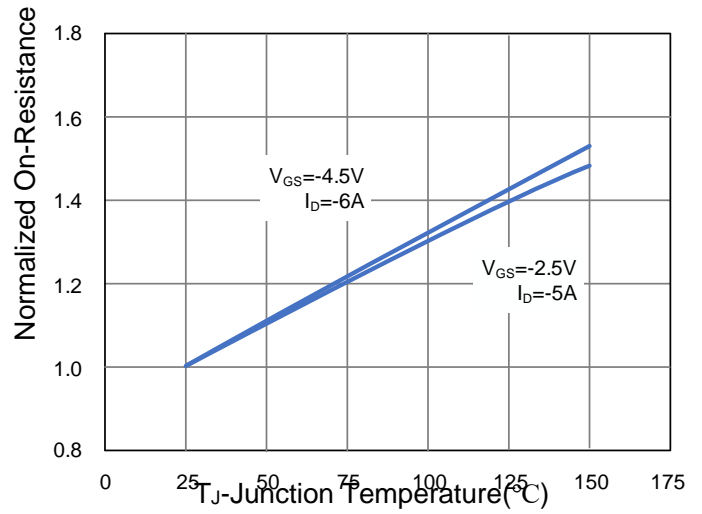


Figure 8 Rdson vs Junction Temperature

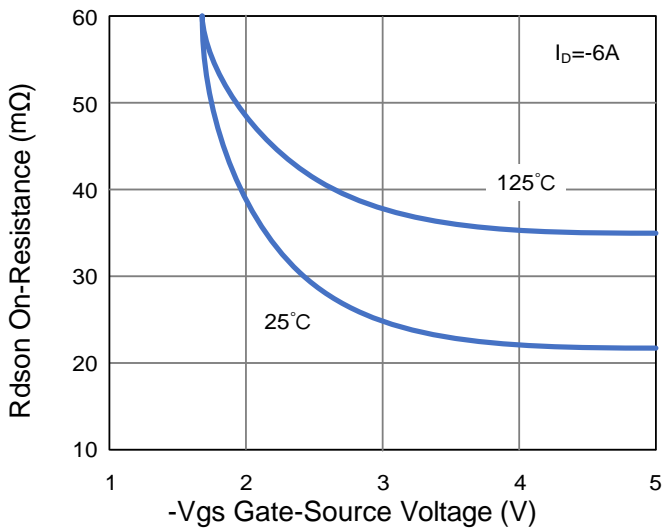


Figure 9 Rdson vs Vgs

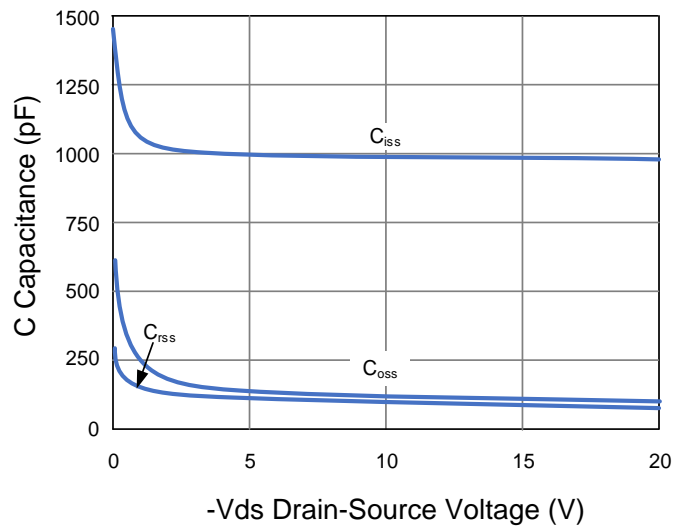


Figure 10 Capacitance vs Vds

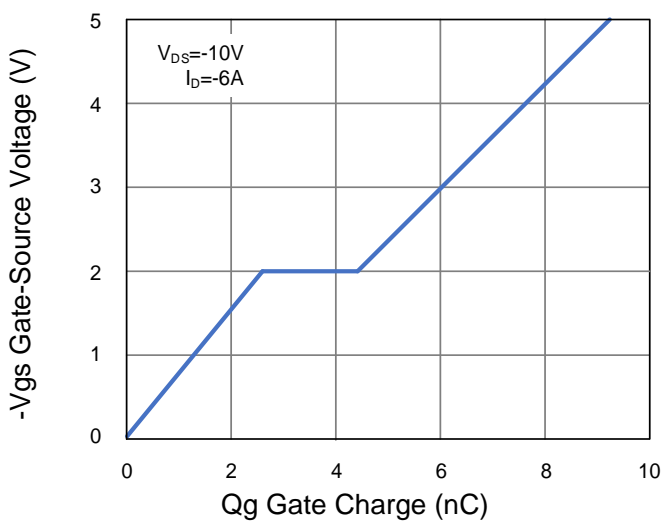


Figure 11 Gate Charge

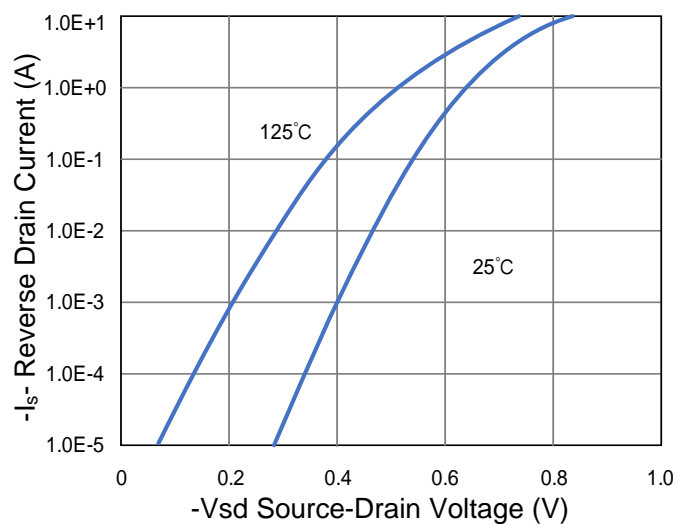


Figure 12 Source- Drain Diode Forward

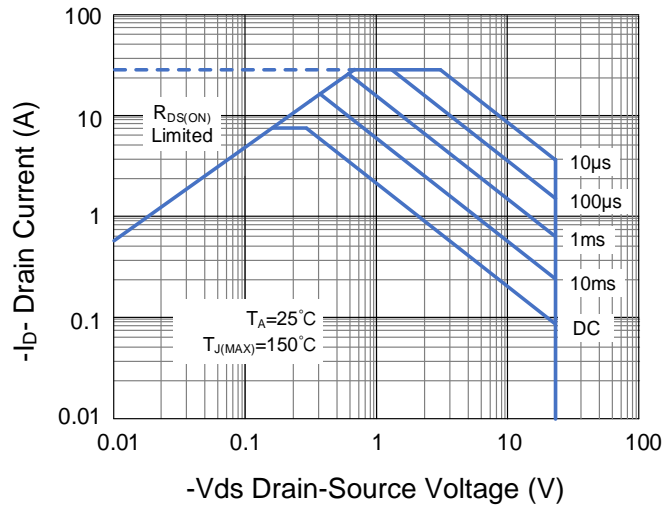


Figure 13 Safe Operation Area

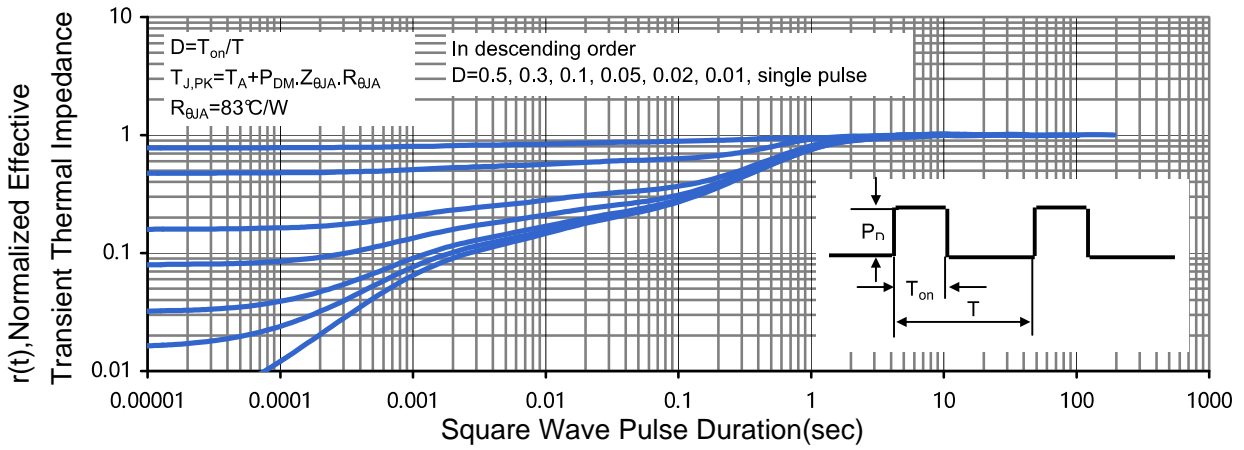


Figure 14 Normalized Maximum Transient Thermal Impedance